Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method of forming a thin metal film, comprising:

preparing a dispersed liquid having a metal-containing organic compound dispersed in a predetermined solvent;

coating said dispersed liquid on a surface of a substrate and evaporating the solvent to form a coating layer;

[[and]]

applying an energy beam to said coating layer to decompose away an organic substance contained in said coating layer in an area irradiated with the energy beam and to bond metal contained in said coating layer; and

dissolving away said metal-containing organic compound left on the surface of the substrate with a solvent.

2. (original) A method of forming a thin metal film according to claim 1, wherein a metal powder is dispersed in said dispersed liquid.

3. (original) A method of forming a thin metal film, comprising:

preparing a dispersed liquid having a metal-containing organic compound dispersed in a predetermined solvent;

coating said dispersed liquid on a surface of a substrate and evaporating the solvent to form a coating layer;

applying an energy beam to said coating layer to decompose away an organic substance contained in said coating layer in an area irradiated with the energy beam and bond metal contained in said coating layer to form a metal pattern; and

dissolving away said metal-containing organic compound left on the surface of the substrate with a solvent.

4. (original) A method of forming a thin metal film according to claim 3, further comprising:

forming an insulating film on the surface of the substrate; and

chemical mechanical polishing the surface of said insulating film.

5. (original) A method of forming a thin metal film according to any one of claims 1 through 4, wherein said metal-containing organic compound comprises ultrafine composite metal particles having a core made substantially of a metal component having an average diameter ranging from 1 to

100 nm and a covering layer of an organic substance chemically bonded to said core, and/or a metal complex.

6. (original) A method of forming a thin metal film according to claim 5, wherein said core made substantially of a metal component has an average diameter ranging from 1 to 20 nm.

7. (previously presented) A method of forming a thin metal film according to claim 1, wherein said energy beam comprises an electron beam, and is applied in air, an inactive gas, or a vacuum.

8. (previously presented) A semiconductor device having interconnects formed by a method of forming a thin metal film according to claim 1.

9-15. (canceled)